YJ Planar Schottky Barrier Diode Die Specification

40V 5A, 70mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB070L040SS-280D

Main Products Characterstics

- Average forward current: IF(AV) = 5 A
- Maximum operating junction temperature: Tj = 125 °C
- ESD rating: >8KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

I_F = 5 A
Pulse Test: tp = 300 μs, δ 2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environment:

Yangjie Electronics